

# New Jersey Semi-Conductor Products, Inc.

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## Triacs

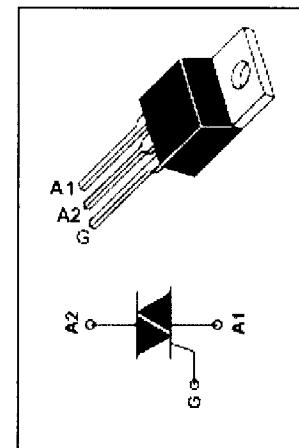
TIC216M

### FEATURES

- With TO-220 package
- Sensitive Gate Triacs
- Glass Passivated
- Max  $I_{GT}$  of 5 mA (Quadrants 1~3)

### ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	MIN	UNIT
$V_{DRM}$	Repetitive peak off-state voltage	600	V
$V_{RRM}$	Repetitive peak reverse voltage	600	V
$I_{T(RMS)}$	RMS on-state current (full sine wave) $T_c=70^\circ C$	6	A
$I_{TSM}$	Non-repetitive peak on-state current	60	A
$T_j$	Operating junction temperature	110	$^\circ C$
$T_{stg}$	Storage temperature	-45~150	$^\circ C$
$R_{th(j-c)}$	Thermal resistance, junction to case	2.5	$^\circ C/W$
$R_{th(j-a)}$	Thermal resistance, junction to ambient	62.5	$^\circ C/W$



### ELECTRICAL CHARACTERISTICS ( $T_c=25^\circ C$ unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS		MAX	UNIT
$I_{DRM}$	Repetitive peak off-state current	$V_D=V_{DRM}, T_c=110^\circ C$		2.0	mA
$I_{GT}$	Gate trigger current	I	$V_{supply} = 12 V \dagger; R_L = 10 \Omega; t_{p(g)} > 20 \mu s$	5	mA
		II		5	
		III		5	
		IV		10	
$I_H$	Holding current	$V_{supply} = 12 V \dagger, I_G = 0$ initial $I_{TM} = 100mA$		30	mA
$V_{GT}$	Gate trigger voltage	I	$V_{supply} = 12 V \dagger; R_L = 10 \Omega; t_{p(g)} > 20 \mu s$	2.2	V
		II		2.2	
		III		2.2	
		IV		3.0	
$V_{TM}$	On-state voltage	$I_T = 8.4A; I_G = 50mA$		1.7	V



Quality Semi-Conductors